

## **General Description**

The AOZ8231B is a one-line bi-directional transient voltage suppressor diode designed to protect voltage sensitive electronics from high transient conditions and ESD.

This device incorporates one TVS diode in an ultra-small DFN package. It may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (±15kV air, ±8kV contact discharge).

The AOZ8231B comes in an RoHS compliant DFN 1.0 x 0.6 package and is rated over a -40°C to +85°C ambient temperature range.

The ultra-small  $1.0 \times 0.6 \times 0.5$ mm DFN package makes it ideal for applications where PCB space is a premium. The small size and high ESD protection makes it ideal for protecting voltage sensitive electronics from high transient conditions and ESD.

#### **Features**

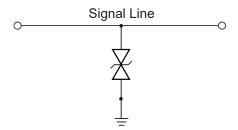
- ESD protection for high-speed data lines:
  - Exceeds: IEC 61000-4-2 (ESD) ±18kV (air), ±18kV (contact)
  - Human Body Model (HBM) ±30kV
  - IEC 61000-4-5 (Lightning) ±4A (8/20µS)
  - IEC 61000-4-4 (EFT) ±40A
- Small package saves board space
- Low insertion loss
- Low clamping voltage
- Operating voltage: 8V
- Pb-free device

### **Applications**

- Portable handheld devices
- Keypads, data lines, buttons
- Notebook computers
- Digital Cameras
- Portable GPS
- MP3 players



# **Typical Application**



**Bidirection Protection of Single Line** 

## **Pin Configuration**





## **Ordering Information**

Part Number	Ambient Temperature Range	Package	Environmental
AOZ8231BDI-08	-40°C to +85°C	DFN 1.0 x 0.6	Green Product



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant. Please visit www.aosmd.com/media/AOSGreenPolicy.pdf for additional information.

## **Absolute Maximum Ratings**

Exceeding the Absolute Maximum ratings may damage the device.

Parameter	Rating
VP – VN	8V
Peak Pulse Current, t <sub>P</sub> = 8/20μs	4A
Storage Temperature (T <sub>S</sub> )	-65°C to +150°C
ESD Rating per IEC61000-4-2, Contact <sup>(1)</sup>	±18kV
ESD Rating per IEC61000-4-2, Air <sup>(1)</sup>	±18kV
ESD Rating per Human Body Model <sup>(2)</sup>	±30kV

#### Notes:

- 1. IEC 61000-4-2 discharge with  $C_{Discharge}$  = 150pF,  $R_{Discharge}$  = 330 $\Omega$ .
- 2. Human Body Discharge per MIL-STD-883, Method 3015  $C_{Discharge}$  = 100pF,  $R_{Discharge}$  = 1.5k $\Omega$ .

## **Maximum Operating Ratings**

Parameter	Rating
Junction Temperature (T <sub>J</sub> )	-40°C to +125°C

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## **Electrical Characteristics**

 $T_A$  = 25°C unless otherwise specified.  $V_F$  = 0.9V Max. @  $I_F$  = 10mA for all types

Symbol	Parameter	Diagram
I <sub>PP</sub>	Reverse Peak Pulse Current, (t <sub>period</sub> = 100ns, t <sub>r</sub> = 1ns)	_
V <sub>CL</sub>	Clamping Voltage @ I <sub>PP</sub>	lan İ
V <sub>RWM</sub>	Working Peak Reverse Voltage	lpp
I <sub>R</sub>	Maximum Reverse Leakage Current	
V <sub>BR</sub>	Breakdown Voltage	V <sub>CL</sub> V <sub>BR</sub> V <sub>RWM</sub>
I <sub>F</sub>	Forward Current	R V <sub>CL</sub> V <sub>BR</sub> V <sub>RWM</sub>
V <sub>F</sub>	Forward Voltage	/
P <sub>PK</sub>	Peak Power Dissipation	Ipp
СЈ	Capacitance @ V <sub>R</sub> = 0 and f = 1MHz	

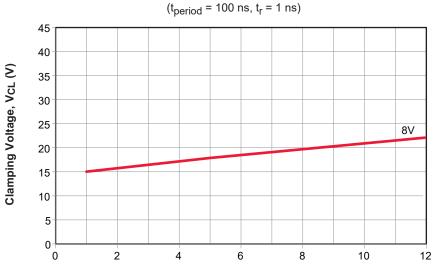
	Dovice	V <sub>RWM</sub> (V)	V <sub>BR</sub> (V)	I <sub>R</sub> (μΑ)	V <sub>CL</sub> Max.			C <sub>J</sub> (pF)	C. (nF)
Device	Device Marking	Max.	Min. @ 1mA	Max.	I <sub>PP</sub> = 1A	I <sub>PP</sub> = 5A	I <sub>PP</sub> = 12A	Typ.	Max.
AOZ8231BDI-08	1	8.0	9.5	0.1	15.0	18	22.5	45	56

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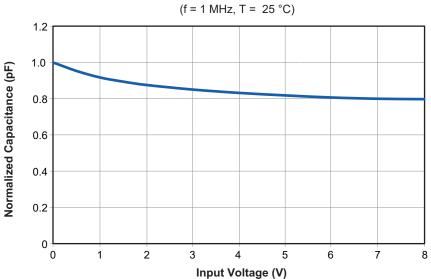
# **Typical Performance Characteristics**

## Clamping Voltage vs. Peak Pulse Current



## Typical Variation of $C_{\text{IN}}$ vs. $V_{\text{R}}$

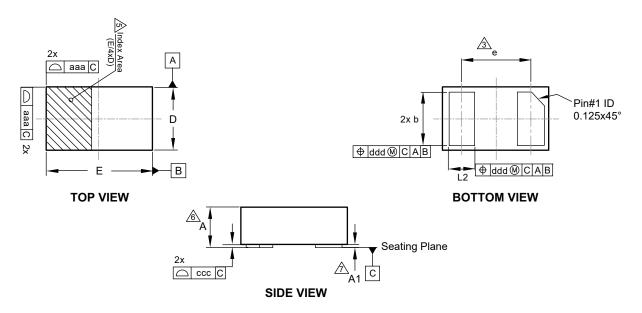
Peak Pulse Current, Ipp (A)



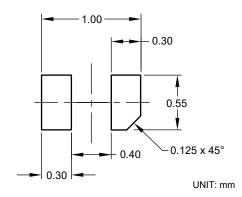
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## Package Dimensions, DFN 1.0 x 0.6



#### **RECOMMENDED LAND PATTERN**



#### **Dimensions in millimeters**

Symbols	Min.	Nom.	Max.				
Α	0.47	0.51	0.55				
A1	0.00	0.02	0.05				
b	0.45	0.50	0.55				
D	0.60 BSC						
E	1.00 BSC						
е	(	).65 BSC	)				
L	0.20	0.25	0.30				
aaa	0.05						
ccc	0.03						
ddd		0.10					

#### **Dimensions in inches**

Symbols	Min.	Nom.	Max.
Α	0.019	0.020	0.022
A1	0.000	0.001	0.002
b	0.018	0.020	0.022
D		0.024	
E		0.039	
е		0.026	
L	0.008	0.010	0.012
aaa		0.002	
ccc		0.001	
ddd		0.004	

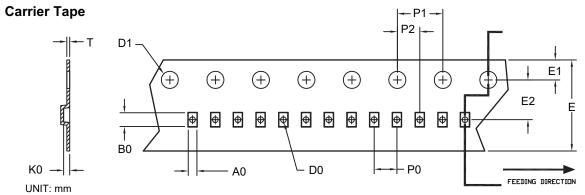
#### Notes:

- 1. Dimensions and tolerancing conform to ASME Y14.5-2009.
- 2. All dimensions are in milliteters.
- <u>A</u> "e" represents the terminal grid pitch.
- 4. N isthe total number of terminals.
- ⚠ A visual index feature must be located within the hatched area. Typical index feature (chamfer) must be located on the edge of the Pin#1 feature.
- This dimension includes stand-off height "A1" and packaged body thickness, but does not include attached feature e.g. external heatsink or chip capacitors, an internal heatslug is not considered as attached feature.
- ⚠ Dimension "A1" is primarily terminal plating, and does not include small metal protrusions.

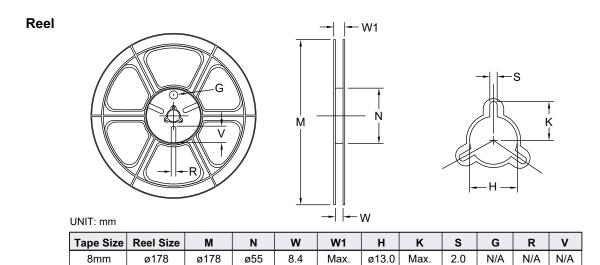
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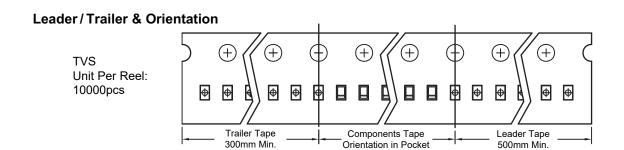


## Tape and Reel Dimensions, DFN 1.0 x 0.6



Option	Package	A0	В0	K0	D0	D1	E	E1	E2	P0	P1	P2	Т
А	DFN 1.0x0.6/ DFN 1.0x0.6A (8 mm)	0.69 ±0.05	1.19 ±0.05	0.66 ±0.05	0.40 ±0.05	1.50 ±0.10	8.00 +0.3/-0.1	1.75 ±0.10	3.50 ±0.05	2.00 ±0.05	4.00 ±0.10	2.00 ±0.05	0.23 ±0.02
В	DFN 1.0x0.6/ DFN 1.0x0.6A (8 mm)	0.65 ±0.04	1.05 ±0.04	0.61 ±0.04	0.40 ±0.05	1.50 ±0.10	8.00 +0.3/-0.1	1.75 ±0.10	3.50 ±0.05	2.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.20 ±0.05





+1.5/-0

14.4

±0.5

10.1

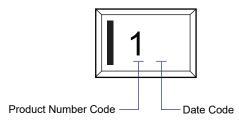
±0.5

±0.5



### Part Marking





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#### LIFE SUPPORT POLICY

ALPHA AND OMEGA SEMICONDUCTOR PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS.

As used herein:

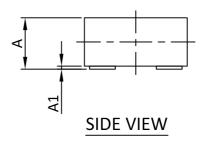
- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

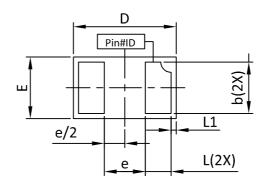
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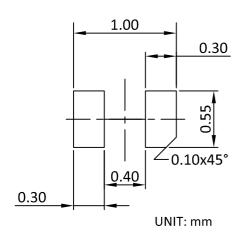
# DFN1.0x0.6\_2L\_EP2\_S PACKAGE OUTLINE





**BOTTOM VIEW** 

### RECOMMENDED LAND PATTERN



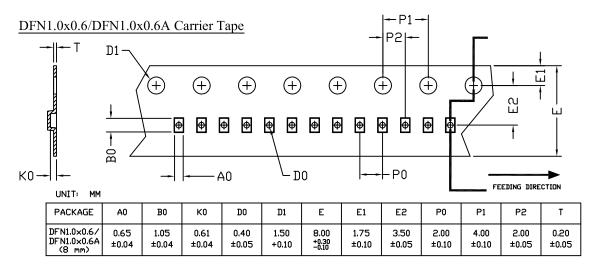
SYMBOLS	DIM	MENSION IN	MM	DIMENSION IN INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.31		0.55	0.012		0.022	
A1	0.00	0.03	0.05	0.000	0.001	0.002	
b	0.45	0.50	0.55	0.018	0.020	0.022	
D	0.95	1.00	1.05	0.037	0.039	0.041	
Е		0.60	-		0.024		
е		0.40	-		0.016		
L	0.20	0.25	0.30	0.008	0.010	0.012	
L1		0.05			0.002		

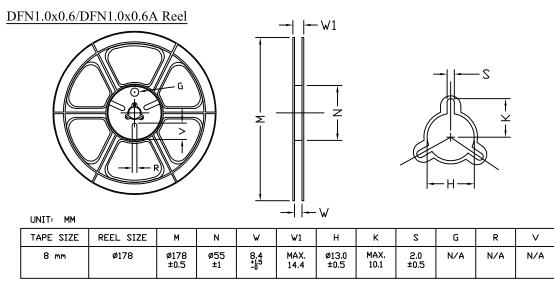
#### NOTE

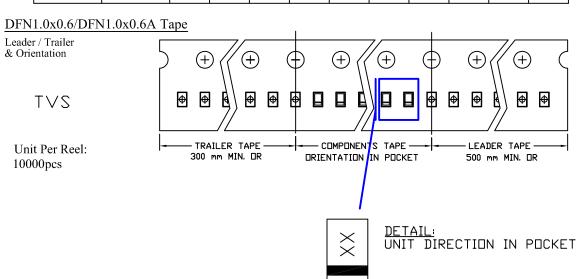
- 1. ALL DIMENSION ARE IN MILLIMETERS.ANGLES ARE IN DEGREES.
- 2. COPLANARITY APPLIES TO THE EXPOSED HEAT SINK SLUG AS WELL AS THE TERMINALS.
- 3. THE SHAPE OF PIN ID CAN BE DIFFERENT PER MANUFACTURING LOCATION & PIN1 NOTCH IS ONLY FOR REFERENCE.



# ALPHA & OMEGA SEMICONDUCTOR DFN1.0x0.6/DFN1.0x0.6A Tape and Reel Data

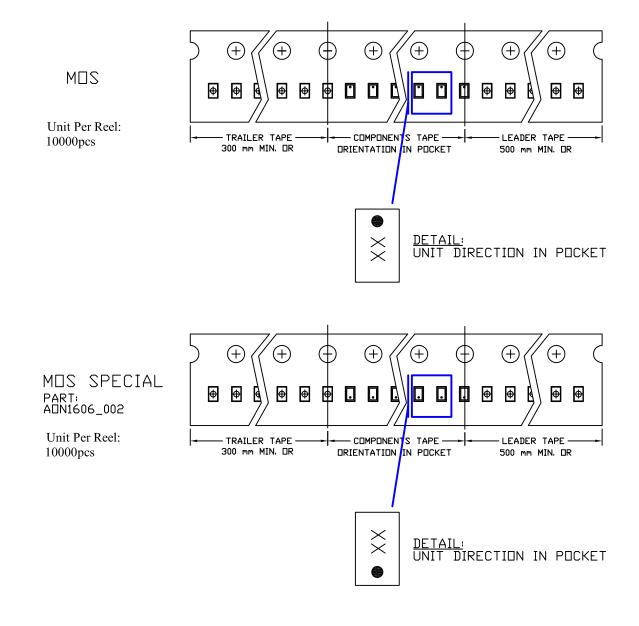








# ALPHA & OMEGA DFN1.0x0.6/DFN1.0x0.6A Tape and Reel Data





# AOS Semiconductor Product Reliability Report

**AOZ8231BDI-08**, rev A

**Plastic Encapsulated Device** 

ALPHA & OMEGA Semiconductor, Inc <a href="https://www.aosmd.com">www.aosmd.com</a>



This AOS product reliability report summarizes the qualification result for AOZ8231BDI-08. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOZ8231BDI-08 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

### I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTRB	Temp = 150°C , Vdd=100% of VRWMmax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
Precondition (Note A)	168hr 85°C / 85%RH + 3 cycle reflow@260°C	-	1386 pcs	0	JESD22-A113
HAST	130°C , 85%RH, 33.3 psia, Vdd = 80% of VRWMmax	96 hours	462 pcs	0	JESD22-A110
Autoclave	121°C , 29.7psia, RH=100%	96 hours	462 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air	250 / 500 cycles	462 pcs	0	JESD22-A104

**Note:** The reliability data presents total of available generic data up to the published date. Note A: MSL (Moisture Sensitivity Level) 1 based on J-STD-020

## II. Reliability Evaluation

FIT rate (per billion): 7.63

**MTTF** = 14960 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = 
$$Chi^2 \times 10^9 / [2 (N) (H) (Af)] = 7.63$$
  
MTTF =  $10^9 / FIT = 14960 \text{ years}$ 

Chi<sup>2</sup> = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from burn-in tests

**H** = Duration of burn-in testing

**Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = Exp [Ea / k (1/Tj u - 1/Tj s)]

**Acceleration Factor ratio list:** 

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

**Tj u** = The use junction temperature in degree (Kelvin), K = C + 273.16

**k** = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>eV / K